2022년 1월 25일(화), 09:00-10:30 Room G (스페이드 II+III, 6층)

J. Nano-Science & Technology 분과 [TG1-J] Neuromorphic Electronics I

좌장: 조병진 교수(충북대학교)

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TG1-J-1 09:00-09:15	Artificial Neuron based on SiO _x Nanorod Structured Memristor for Probabilistic Computing Application Sanghyeon Choi ¹ , Gwang Su Kim ^{1,2} , Jehyeon Yang ¹ , Haein Cho ¹ , Chong-Yun Kang ^{1,2} , and Gunuk Wang ^{1,3} ¹ KU-KIST Graduate School of Converging Science and Technology, Korea University, ² Electronic Materials Research Center, KIST, ³ Department of Integrative Energy Engineering, Korea University
TG1-J-2 09:15-09:45	Ferroelectric Materials for Memory and Neuromorphic Device Applications Jang-Sik Lee Department of Materials Science and Engineering, POSTECH
TG1-J-3 09:45-10:00	Effect of HfO ₂ Passivation Layer on Photosynaptic Functionality of InGaZnO Synaptic Device Seyoung Oh ¹ and Byungjin Cho ^{1,2} ¹ Department of Advanced Material Engineering, Chungbuk National University, ² Department of Urban, Energy, Environmental Engineering, Chungbuk National University
TG1-J-4 10:00-10:15	Synaptic Device based on Resistive Switching Memory Using Single Walled Carbon Nanotube Dong Jun Jang, Hyunwoo Ryu, Hyeonjin Cha, Na-Young Lee, Younglae Kim, and Min-Woo Kwon Department of Electric Engineering, Gangneung-Wonju National University
TG1-J-5 10:15-10:30	Organic Ion Reservoirs for Synaptic Memory Devices Dongshin Kim, Ik-Jyae Kim, and Jang-Sik Lee Department of Materials Science and Engineering, POSTECH